

IN THE SPECIFICATION

Please replace the paragraph at page 2, lines 8-20, with the following rewritten paragraph:

If a depo-process is followed by a depoless-process in a same chamber while dry etching a silicon oxide film, an etching rate of the depoless-process becomes unstable, since the depoless-process can be easily influenced by deposits produced in the same chamber during the preceding depo-process. The term "depo-process" used herein denotes a process of using a gas with a ~~smaller~~ an F/C (fluorine/chlorine) ratio, e.g., C_4F_8 , which leaves a visible amount of polymers including a CF based ~~element~~ component such as CF_4 attached to the chamber. The term "depoless-process" used herein denotes a process using a gas with a larger (relative to the "depo-process") F/C ratio, e.g., CF_4 , which leaves no polymers attached to the chamber.